L Number	Hits	Search Text	DB	Time stamp
1	184		USPAT;	2004/07/22 08:16
-	104	barrier same copper same anneal\$6 same (reducing or (forming adj gas) or ammonia or	US-PGPUB;	2004/01/22 00:10
		nitrogen or ("nh.sub.3") or ("n.sub.2"))	EPO; JPO;	
			DERWENT; IBM TDB	
2	94	(barrier same copper same anneal\$6 same	USPAT;	2004/07/22 08:16
2	94	(reducing or (forming adj gas) or ammonia or	US-PGPUB;	2004/07/22 08:10
		nitrogen or ("nh.sub.3") or ("n.sub.2")))	EPO; JPO;	
		and @ad<=20010417	DERWENT;	1
		and Gad-20010417	IBM TDB	
_	833	438/618	USPAT;	2003/03/10 10:42
	033	130,010	EPO; JPO;	2003,03,10 20112
			DERWENT	
-	672	438/633	USPAT;	2001/12/17 14:40
			EPO; JPO;	
			DERWENT	l
-	45384	barrier adj (layer or film)	USPAT;	2001/12/18 14:06
			EPO; JPO;	
			DERWENT	
-	1055	(barrier adj (layer or film)) and (reduc\$4	USPAT;	2004/03/02 08:58
		adj (gas or agent or chemical))	EPO; JPO;	
[			DERWENT	
-	237		USPAT;	2001/12/18 08:17
		adj (gas or agent or chemical))) and (metal	EPO; JPO;	
		adj (film or layer))	DERWENT	
-	5	(barrier adj (layer or film)) and (first adj	USPAT;	2001/12/17 14:56
		reduc\$4 adj (gas or agent or chemical))	EPO; JPO;	
			DERWENT	
-	0	((barrier adj (layer or film)) and (first	USPAT;	2001/12/17 14:53
		adj reduc\$4 adj (gas or agent or chemical)))	EPO; JPO;	
i	_	and (metal adj (film or layer))	DERWENT	
-	0	(((barrier adj (layer or film)) and (reduc\$4	USPAT;	2001/12/17 14:55
		adj (gas or agent or chemical))) and (metal	EPO; JPO;	
		adj (film or layer))) and (second adj	DERWENT	
		reduc\$4 adj (gas or agent or chemical))		
-	237	(((barrier adj (layer or film)) and (reduc\$4	USPAT;	2001/12/17 14:55
		adj (gas or agent or chemical))) and (metal	EPO; JPO;	
		adj (film or layer))) and (reduc\$4 adj (gas	DERWENT	
	163	or agent or chemical)) (first adj reduc\$4 adj (gas or agent or	USPAT;	2001/12/17 14:58
	103	chemical))	EPO; JPO;	2001/12/1/ 14:58
		Chemical,	DERWENT	İ
_	92	((first adj reduc\$4 adj (gas or agent or	USPAT;	2001/12/17 15:01
	22	chemical))) and (second adj reduc\$4 adj (gas	EPO; JPO;	1001, 12, 1, 13.01
		or agent or chemical))	DERWENT	
_	6	l <del>T</del>	USPAT;	2001/12/17 15:01
	•	chemical))) and (second adj reduc\$4 adj (gas	EPO; JPO;	,,
		or agent or chemical))) and semiconductor	DERWENT	
-	683	438/627	USPAT;	2001/12/17 15:31
			EPO; JPO;	
			DERWENT	
-	1178	438/643	USPAT;	2002/01/02 14:19
			EPO; JPO;	
			DERWENT	
-	20851	(((diffus\$6 adj barrier) or prevent\$10) adj	USPAT;	2001/12/18 14:01
		(layer or film))	EPO; JPO;	
			DERWENT	
-	394	((((diffus\$6 adj barrier) or prevent\$10) adj	USPAT;	2001/12/18 08:17
		(layer or film))) and (reduc\$4 adj (gas or	EPO; JPO;	
		agent or chemical))	DERWENT	
-	96	((((diffus\$6 adj barrier) or prevent\$10)	USPAT;	2001/12/18 12:54
		adj (layer or film))) and (reduc\$4 adj (gas	EPO; JPO;	
		or agent or chemical))) and (metal adj (film	DERWENT	
_	20051	or layer))	HODE	2001/10/10 11 15
_	20851	(((diffus\$6 adj barrier) or prevent\$10) adj	USPAT;	2001/12/18 14:02
İ		(layer or film))	EPO; JPO;	
_	3447	(((diffuece adi harriar) or (diffuece adi	DERWENT	2001/12/10 14 04
	344/	(((diffus\$6 adj barrier) or (diffus\$6 adj prevent\$10)) adj (layer or film))	USPAT;	2001/12/18 14:04
		prevencaro,, auj (rayer or riim))	EPO; JPO;	
	<del></del>		DERWENT	<u> </u>

-	40	((((diffus\$6 adj barrier) or prevent\$10) adj (layer or film)) ) and (first adj anneal\$5)	USPAT; EPO; JPO;	2001/12/18 14:07
-	0	((((diffus\$6 adj barrier) or prevent\$10) adj (layer or film)) ) and (first adj	DERWENT USPAT; EPO; JPO;	2001/12/18 14:08
-	45418	anneal\$5)) and (second adj aneal\$5) barrier adj (layer or film)	DERWENT USPAT;	2003/03/07 13:53
-	147	(barrier adj (layer or film) ) and (first adj anneal\$5)	EPO; JPO; DERWENT USPAT;	2001/12/18 14:08
-	0	((barrier adj (layer or film) ) and (first	EPO; JPO; DERWENT USPAT;	2001/12/18 14:21
_	483098	adj anneal\$5)) and (second adj aneal\$5)  plug or interconnection	EPO; JPO; DERWENT USPAT;	2001/12/18 14:23
			EPO; JPO; DERWENT	
-	108014	metal adj (layer or film)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:24
-	18975	(metal adj (layer or film)) and (plug or interconnect\$5)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:25
-	3544	((metal adj (layer or film)) and (plug or interconnect\$5)) and anneal\$5	USPAT; EPO; JPO; DERWENT	2001/12/18 14:25
-	56	interconnect\$5)) and anneal\$5) and (reduc\$3	USPAT; EPO; JPO;	2001/12/18 14:30
-	6	adj atmosphere) ((barrier adj (layer or film) ) and (first adj anneal\$5)) and (reduc\$3 adj atmosphere)	DERWENT USPAT; EPO; JPO;	2001/12/18 14:31
_	40	interconnect\$5)) and anneal\$5) and (reduc\$3	DERWENT USPAT; EPO; JPO;	2001/12/18 14:37
_	6	adj atmosphere)) and semiconductor (((barrier adj (layer or film)) and (first adj anneal\$5)) and (reduc\$3 adj atmosphere))	DERWENT USPAT; EPO; JPO;	2001/12/18 14:36
-	5	and semiconductor (("5116463") or ("6207222") or ("6197688") or ("6191031") or ("6143646")).PN.	DERWENT USPAT	2004/07/22 09:35
_	562	438/687	USPAT; EPO; JPO; DERWENT	2004/02/20 13:52
_	55733	barrier adj (layer or film)	USPAT; US-PGPUB; EPO; JPO;	2003/03/10 07:56
_	489	(barrier adj (layer or film)) and (reduc\$3	DERWENT; IBM_TDB USPAT;	2003/03/07 14:01
		adj (gas or ambient))	US-PGPUB; EPO; JPO; DERWENT;	
_	160	((barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient))) and (metal adj (layer or film))	IBM_TDB USPAT; US-PGPUB;	2003/03/07 14:03
			EPO; JPO; DERWENT; IBM_TDB	2002/02/05
_	3	(((barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient))) and (metal adj (layer or film))) and (second adj (gas or ambient))	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/07 14:08
-	222	(barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient)) and plasma	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/03/07 14:05
		<del></del>	DERWENT; IBM_TDB	

	·			·
-	3	((((barrier adj (layer or film)) and	USPAT;	2003/03/07 13:59
		(reduc\$3 adj (gas or ambient))) and (metal	US-PGPUB;	
		adj (layer or film))) and (second adj (gas	EPO; JPO;	
		or ambient))) and plasma	DERWENT; IBM TDB	
_	113	(((barrier adj (layer or film)) and (reduc\$3	USPAT;	2003/03/07 14:06
		adj (gas or ambient))) and (metal adj (layer	US-PGPUB;	2003,03,0, 11:00
		or film))) and plasma	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	28226	J	USPAT;	2003/03/07 14:03
		or (hygrogen or ("H.sub.2")) adj (gas or	US-PGPUB;	
		ambient))	EPO; JPO;	
			DERWENT;	
	6490	((barrior add (layer or film)) and (moduce)	IBM_TDB	2002/02/07 14:05
-	0490	((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or	USPAT; US-PGPUB;	2003/03/07 14:05
		ambient))) and (metal adj (layer or film))	EPO; JPO;	
		discrete, , , and (metal ad) (rayer or rilling,	DERWENT;	
			IBM TDB	
-	222	((barrier adj (layer or film)) and (reduc\$3	USPAT;	2003/03/07 14:07
		or (hygrogen or ("H.sub.2")) adj (gas or	US-PGPUB;	
		ambient))) and (reduc\$3 adj (gas or	EPO; JPO;	
		ambient)) and plasma	DERWENT;	
	03.05	//bosssion add /lossss on 500000 and /orders	IBM_TDB	0000/00/00
_	8105	((barrier adj (layer or film)) and (reduc\$3	USPAT;	2003/03/07 14:07
		or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and plasma	US-PGPUB; EPO; JPO;	
		ambrency,, and prasma	DERWENT;	
			IBM TDB	
-	3403	(((barrier adj (layer or film)) and (reduc\$3	USPAT;	2003/03/07 14:07
		or (hygrogen or ("H.sub.2")) adj (gas or	US-PGPUB;	
		ambient))) and (metal adj (layer or film)))	EPO; JPO;	
		and plasma	DERWENT;	
			IBM_TDB	
_	99	1	USPAT;	2003/03/07 14:07
		or (hygrogen or ("H.sub.2")) adj (gas or	US-PGPUB;	
		ambient))) and (metal adj (layer or film))) and (second adj (gas or ambient))	EPO; JPO; DERWENT;	
		and (become day (gab of ambfelle))	IBM TDB	
-	99	((((barrier adj (layer or film)) and	USPAT;	2003/03/07 14:10
		(reduc\$3 or (hygrogen or ("H.sub.2")) adj	US-PGPUB;	
		(gas or ambient))) and (metal adj (layer or	EPO; JPO;	
		film))) and (second adj (gas or ambient)))	DERWENT;	
		and (second adj (gas or ambient))	IBM_TDB	
_	92	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2003/03/07 14:10
		(reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (metal adj (layer or	US-PGPUB;	
		film))) and (second adj (gas or ambient)))	EPO; JPO; DERWENT;	
		and (second adj (gas or ambient))) and	IBM_TDB	
		semiconductor		
-	25099		USPAT	2003/03/10 07:56
-	7320	(barrier adj (layer or film)) and ((expos\$3	USPAT	2003/03/10 08:01
		or anneal\$5) and ((reduc\$3 adj gases) or		
_	2056	(hydrogen or ("H.sub.2")))) ((harrier adi (laver or film)) and ((ornogen	TIODAM	2002/02/20 02 05
_	3856	((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or	USPAT	2003/03/10 08:02
		(hydrogen or ("H.sub.2"))))) and		
		semiconductor		
-	1694		USPAT	2003/03/10 08:03
İ		((expos\$3 or anneal\$5) and ((reduc\$3 adj		, ,
		gases) or (hydrogen or ("H.sub.2"))))) and		
		semiconductor) and (metal adj (layer or		
_	3.03	film)) ///barrior add /laver or film)) and	110010	0000 100 100
-	303		USPAT	2003/03/10 08:04
		((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and		
		semiconductor) and ((metal adj (layer or		
		film)) same (chemical adj vapor adj		
		deposition))	<b> </b>	
<u></u>		· · · · · · · · · · · · · · · · · · ·	<del></del>	

_	60	((((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and	USPAT	2003/03/10 08:05
		semiconductor) and (metal adj (layer or film))) and (second adj gas)		
-	9	((((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and	USPAT	2004/02/20 13:52
		semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))) and (second adj gas)		
_	2	(("5665659") or ("5953634")).PN.	USPAT	2004/02/23 09:53
-	1	("6475902").PN.	USPAT	2003/11/17 07:10
-	1	("20020009872").PN.	US-PGPUB	2003/11/14 16:12
_	3	("6303959")).PN.	USPAT; US-PGPUB	2003/11/17 06:46
-	10	<pre>((((barrier adj (layer or film)) and   ((expos\$3 or anneal\$5) and ((reduc\$3 adj   gases) or (hydrogen or ("H.sub.2")))) and   semiconductor) and ((metal adj (layer or   film)) same (chemical adj vapor adj   deposition))) and (second adj gas)</pre>	USPAT	2004/02/20 13:53
_	1661	438/687	USPAT;	2004/02/20 13:52
			US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13.32
-	1884	438/618	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 13:52
-	1281	438/633	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/20 13:52
-	1407	438/627	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/20 13:53
-	1772	438/643	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20 13:53
-	1661	438/687	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20 13:53
_	2	438/687,618,633,627,643,687.CCLS. and	DERWENT; IBM_TDB USPAT;	2004/03/02 13:03
		<pre>((((barrier adj (layer or film)) and   ((expos\$3 or anneal\$5) and ((reduc\$3 adj   gases) or (hydrogen or ("H.sub.2"))))) and   semiconductor) and ((metal adj (layer or   film)) same (chemical adj vapor adj   deposition))) and (second adj gas) and   @ad&lt;=20010417</pre>	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/02 13:03
_	8	438/\$.CCLS. and ((((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))) and (second adj gas) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:58

			· [	
-	8	257/\$.CCLS. and (((barrier adj (layer or	USPAT;	2004/02/20 13:59
		film)) and ((expos\$3 or anneal\$5) and	US-PGPUB;	
		((reduc\$3 adj gases) or (hydrogen or	EPO; JPO;	
		("H.sub.2")))) and semiconductor) and	DERWENT;	
		((metal adj (layer or film)) same (chemical	IBM_TDB	
		adj vapor adj deposition))) and (second adj	_	
		gas) and @ad<=20010417		
_	11	((((barrier adj (layer or film)) and	USPAT;	2004/02/20 13:59
		((expos\$3 or anneal\$5) and ((reduc\$3 adj	US-PGPUB;	
		gases) or (hydrogen or ("H.sub.2"))))) and	EPO; JPO;	
		semiconductor) and ((metal adj (layer or	DERWENT;	
		film)) same (chemical adj vapor adj	IBM TDB	
		1	1511_106	
1		deposition))) and (second adj gas) and		
}	_	@ad<=20010417		0004/00/00 00
-	5		USPAT	2004/02/23 08:02
		"5900498"   "5908947").PN.		
-	2508		USPAT;	2004/03/02 09:01
		and (metal adj (layer or film)) and (treat\$6	EPO; JPO;	
	İ	or ((post adj treat\$6) or (post-treat\$6) or	DERWENT	
		(posttreat\$6)))		!
-	2198	(barrier adj (layer or film)) and (reduc\$4)	USPAT;	2004/03/02 09:02
		and (metal adj (layer or film)) and (treat\$6	EPO; JPO;	, , , , , , , , , , , , , , , , , , , ,
		or ((post adj treat\$6) or (post-treat\$6) or	DERWENT	
		(posttreat\$6))) and @ad<=20010417		
_	1610	1 -	IICDAM -	2004/02/02 00 10
	1012	semiconductor and (barrier adj (layer or	USPAT;	2004/03/02 09:12
		film)) and (reduc\$4) and (metal adj (layer	EPO; JPO;	
		or film)) and (treat\$6 or ((post adj	DERWENT	
		treat\$6) or (post-treat\$6) or		
	•	(posttreat\$6))) and @ad<=20010417	ļ	
-	1416	(semiconductor and (barrier adj (layer or	USPAT;	2004/03/02 09:13
j		film)) and (reduc\$4) and (metal adj (layer	EPO; JPO;	
		or film)) and (treat\$6 or ((post adj	DERWENT	
		treat\$6) or (post-treat\$6) or		
		(posttreat\$6))) and @ad<=20010417 ) and	İ	
		expos\$6		
_	1416		USPAT;	2004/03/02 09:15
		film)) and (reduc\$4) and (metal adj (layer	EPO; JPO;	2001, 03, 02 03.13
		or film)) and (treat\$6 or ((post adj	DERWENT	
		treat\$6) or (post-treat\$6) or	DERWENT	
		_		
		(posttreat\$6))) and @ad<=20010417 ) and		
		expos\$6) and reduc\$6	IIODAM	2004/02/02 20 52
_	1	("5,953,634").PN.	USPAT	2004/03/02 12:53
_	1	("5,665,659").PN.	USPAT	2004/03/02 12:53
-	2	438/687,618,633,627,643,687.CCLS. and	USPAT;	2004/03/08 08:00
		((((barrier adj (layer or film)) and	US-PGPUB;	
		((expos\$3 or anneal\$5) and ((reduc\$3 adj	EPO; JPO;	
		gases) or (hydrogen or ("H.sub.2"))))) and	DERWENT;	
	ļ	semiconductor) and ((metal adj (layer or	IBM_TDB	
	[	film)) same (chemical adj vapor adj	_	
		deposition))) and (second adj gas) and		
		@ad<=20010417		
-	528		USPAT;	2004/03/08 08:03
		((barrier or diffus\$5) adj (layer or film))	US-PGPUB;	
		and (expos\$3 or treat\$6) and ((reduc\$3 adj	EPO; JPO;	
		gases) or (hydrogen or ("H.sub.2"))) and		
	!	@ad<=20010417	DERWENT;	
	3400		IBM_TDB	2004/02/02 22 25
_	3489	, , , , , , , , , , , , , , , , , , ,	USPAT;	2004/03/08 08:03
		(layer or film)) and (expos\$3 or treat\$6)	US-PGPUB;	
		and ((reduc\$3 adj gases) or (hydrogen or	EPO; JPO;	
		("H.sub.2"))) and @ad<=20010417	DERWENT;	
			IBM_TDB	
-	498	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2004/03/08 08:04
		(barrier adj (layer or film)) and (expos\$3	US-PGPUB;	
		or treat\$6) and ((reduc\$3 adj gases) or	EPO; JPO;	
		(hydrogen or ("H.sub.2"))) and @ad<=20010417	DERWENT;	
			IBM TDB	
_	239	438/687,618,633,627,643,687.CCLS. and	USPAT;	2004/07/15 14:40
	239	(barrier adj (layer or film)) and ((expos\$3	1	2004/07/13 14:40
			US-PGPUB;	
		or treat\$6) same ((reduc\$3 adj gases) or	EPO; JPO;	
		(hydrogen or ("H.sub.2")))) and	DERWENT;	
	_	@ad<=20010417	IBM_TDB	
'	1	("6475902").PN.	USPAT	2004/03/08 11:14

				_ ,
-	2		USPAT	2004/07/16 12:19
-	885		USPAT;	2004/07/16 07:04
		((barrier or (diffus\$6 adj prevent\$6)) same	US-PGPUB;	
<u> </u>		(reduc\$3 adj gases) or (hydrogen or	EPO; JPO;	
		("H.sub.2"))) and @ad<=20010417	DERWENT;	]
			IBM_TDB	
-	260		USPAT;	2004/07/16 11:07
		((barrier or (diffus\$6 adj prevent\$6)) same	US-PGPUB;	
		((reduc\$3 adj gases) or (hydrogen or	EPO; JPO;	
		("H.sub.2")))) and @ad<=20010417	DERWENT;	
	_		IBM_TDB	
<u> </u>	1	438/687,618,633,627,643,687.CCLS. and	USPAT;	2004/07/16 08:27
		((barrier or (diffus\$6 adj prevent\$6)) same	US-PGPUB;	
		((reduc\$3 adj gases) or (hydrogen or	EPO; JPO;	
		("H.sub.2")))) and ((free or without or no)	DERWENT;	1
	12	adj plasma) and @ad<=20010417	IBM_TDB	2004/07/16 00:07
-	13	438/\$.CCLS. and ((barrier or (diffus\$6 adj	USPAT;	2004/07/16 09:07
		prevent\$6)) with ((reduc\$3 adj gases) or	US-PGPUB;	
		(hydrogen or ("H.sub.2")))) and ((free or	EPO; JPO;	
		without or no) adj plasma) and @ad<=20010417	DERWENT;	
_	15	257/6 CCIC and //harrion on /diffusec adi	IBM_TDB	2004/07/16 00:07
_	15		USPAT;	2004/07/16 09:07
		prevent\$6)) with ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and ((free or	US-PGPUB; EPO; JPO;	
		without or no) adj plasma) and @ad<=20010417	, ,	
		without of no, adj plasma, and @ad<=20010417	DERWENT;	
l _	10	semiconductor and ((barrier or (diffus\$6 adj	IBM_TDB USPAT;	2004/07/16 12:25
_	10	prevent\$6)) with ((reduc\$3 adj gases) or	US-PGPUB;	2004/07/16 13:25
		(hydrogen or ("H.sub.2")))) and ((free or	EPO; JPO;	
		without or no) adj plasma) and @ad<=20010417	DERWENT;	
		without of no, adj plasma, and wadt=20010417	IBM TDB	
_	35	438/\$.CCLS. and ((barrier or (diffus\$6 adj	USPAT;	2004/07/16 09:08
		prevent\$6)) same ((reduc\$3 adj gases) or	US-PGPUB;	2004/07/16 09:08
		(hydrogen or ("H.sub.2")))) and ((free or	EPO; JPO;	
		without or no) adj plasma) and @ad<=20010417	DERWENT;	
		wronodo or no, daj prabila, dna gad-2001041,	IBM TDB	[
_	42	257/\$.CCLS. and ((barrier or (diffus\$6 adj	USPAT;	2004/07/16 09:08
İ	]	prevent\$6)) same ((reduc\$3 adj gases) or	US-PGPUB;	2004/07/10 03:00
		(hydrogen or ("H.sub.2")))) and ((free or	EPO; JPO;	
		without or no) adj plasma) and @ad<=20010417	DERWENT;	
			IBM TDB	
_	51	semiconductor and ((barrier or (diffus\$6 adj	USPAT;	2004/07/16 09:08
		prevent\$6)) same ((reduc\$3 adj gases) or	US-PGPUB;	
ĺ		(hydrogen or ("H.sub.2")))) and ((free or	EPO; JPO;	
		without or no) adj plasma) and @ad<=20010417	DERWENT;	
			IBM TDB	
-	543	438/687,618,633,627,643,687.CCLS. and	USPAT;	2004/07/16 11:09
		((barrier or (diffus\$6 adj prevent\$6)) same	US-PGPUB;	
		((reduc\$3 adj gases) or (nitrogen or	EPO; JPO;	
	[	("n.sub.2")) or (hydrogen or ("H.sub.2"))))	DERWENT;	
		and @ad<=20010417	IBM_TDB	
-	275		USPAT;	2004/07/16 11:09
		((barrier or (diffus\$6 adj prevent\$6)) same	US-PGPUB;	
		((reduc\$3 adj gases) or (nitrogen or	EPO; JPO;	
		("n.sub.2")) or (hydrogen or ("H.sub.2"))))	DERWENT;	
	]	and anneal\$5 and @ad<=20010417	IBM_TDB	
_	275	438/687,618,633,627,643,687.CCLS. and	USPAT;	2004/07/16 11:10
		((barrier or (diffus\$6 adj prevent\$6)) same	US-PGPUB;	
	[	((reduc\$3 adj gases) or (nitrogen or	EPO; JPO;	
		("n.sub.2")) or (hydrogen or ("H.sub.2")))	DERWENT;	
		and anneal\$5) and @ad<=20010417	IBM_TDB	
	190	438/\$.CCLS. and ((barrier or (diffus\$6 adj	USPAT;	2004/07/16 11:11
		prevent\$6)) with ((reduc\$3 adj gases) or	US-PGPUB;	
!		(nitrogen or ("n.sub.2")) or (hydrogen or	EPO; JPO;	
		("H.sub.2"))) with anneal\$5) and	DERWENT;	
		@ad<=20010417	IBM_TDB	0004105155
-	686	438/\$.CCLS. and ((barrier or (diffus\$6 adj	USPAT;	2004/07/16 11:12
-		prevent\$6)) same ((reduc\$3 adj gases) or	US-PGPUB;	
	[	(nitrogen or ("n.sub.2")) or (hydrogen or	EPO; JPO;	
		("H.sub.2"))) same anneal\$5) and	DERWENT;	
	l <u> </u>	@ad<=20010417	IBM_TDB	

···		· · · · · · · · · · · · · · · · · · ·		
-	938	257/\$.CCLS. and ((barrier or (diffus\$6 adj	USPAT;	2004/07/16 11:12
		prevent\$6)) same ((reduc\$3 adj gases) or	US-PGPUB;	
		(nitrogen or ("n.sub.2")) or (hydrogen or	EPO; JPO;	
		("H.sub.2"))) same anneal\$5) and	DERWENT;	
		@ad<=20010417	IBM_TDB	
-	256	257/\$.CCLS. and ((barrier or (diffus\$6 adj	USPAT;	2004/07/16 11:13
		prevent\$6)) with ((reduc\$3 adj gases) or	US-PGPUB;	
		(nitrogen or ("n.sub.2")) or (hydrogen or	EPO; JPO;	
		("H.sub.2"))) with anneal\$5) and	DERWENT;	
		@ad<=20010417	IBM_TDB	
-	303	semiconductor and ((barrier or (diffus\$6 adj	USPAT;	2004/07/16 11:13
		prevent\$6)) with ((reduc\$3 adj gases) or	US-PGPUB;	
		(nitrogen or ("n.sub.2")) or (hydrogen or	EPO; JPO;	
		("H.sub.2"))) with anneal\$5) and	DERWENT;	
		@ad<=20010417	IBM_TDB	
-	1034	semiconductor and ((barrier or (diffus\$6 adj	USPAT;	2004/07/16 11:13
		prevent\$6)) same ((reduc\$3 adj gases) or	US-PGPUB;	
		(nitrogen or ("n.sub.2")) or (hydrogen or	EPO; JPO;	
		("H.sub.2"))) same anneal\$5) and	DERWENT;	
<u> </u>		@ad<=20010417	IBM_TDB	
	144	438/687,618,633,627,643,687.CCLS. and	USPAT;	2004/07/16 13:19
		((barrier or (diffus\$6 adj prevent\$6)) same	US-PGPUB;	
		((reduc\$3 adj gases) or (nitrogen or	EPO; JPO;	
		("n.sub.2")) or (hydrogen or ("H.sub.2")))	DERWENT;	
		same anneal\$5) and @ad<=20010417	IBM_TDB	
-	0	20020009872.URPN.	USPAT	2004/07/16 13:48
-	12	semiconductor and ((barrier or (diffus\$6 adj	USPAT;	2004/07/16 13:26
		prevent\$6)) with ((reduc\$3 adj gases) or	US-PGPUB;	
		(hydrogen or ("H.sub.2")))) and anneal\$6 and	EPO; JPO;	
		((free or without or no) adj plasma) and	DERWENT;	
		@ad<=20010417	IBM_TDB	
-	32	,	USPAT;	2004/07/16 13:26
İ		prevent\$6)) same ((reduc\$3 adj gases) or	US-PGPUB;	
		(hydrogen or ("H.sub.2")))) and anneal\$6 and	EPO; JPO;	
		((free or without or no) adj plasma) and	DERWENT;	
		@ad<=20010417	IBM_TDB	
-	37		USPAT;	2004/07/16 13:48
		((barrier or (diffus\$6 adj prevent\$6)) with	US-PGPUB;	
		((reduc\$3 adj gases) or (nitrogen or	EPO; JPO;	
		("n.sub.2")) or (hydrogen or ("H.sub.2")))	DERWENT;	
	_	with anneal\$5) and @ad<=20010417	IBM_TDB	
-	8	"6214730"	USPAT	2004/07/16 13:48
<del>-</del>	1	("6214730").PN.	USPAT	2004/07/21 14:33
-	1	("6310300").PN.	USPAT	2004/07/16 13:56
-		("6355558").PN.	USPAT	2004/07/16 13:56
_	6	(("6159857") or ("6350688") or	USPAT;	2004/07/22 08:13
		("20030015793") or ("20030034251") or	US-PGPUB	
		("6479340") or ("20020025694")).PN.	1	